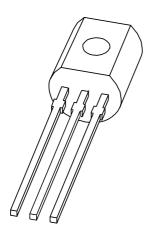
DISCRETE SEMICONDUCTORS

DATA SHEET



MPSA42; MPSA43 NPN high-voltage transistors

Product data sheet Supersedes data of 1999 Apr 12

2004 Oct 11



NPN high-voltage transistors

MPSA42; MPSA43

FEATURES

- Low current (max. 100 mA)
- High voltage (max. 300 V).

APPLICATIONS

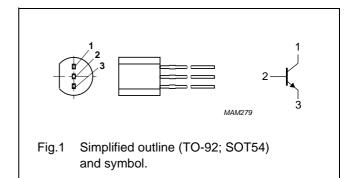
- Video
- Telephony
- Professional communication equipment.

DESCRIPTION

NPN high-voltage transistor in a TO-92; SOT54 plastic package. PNP complement: MPSA92.

PINNING

PIN	DESCRIPTION
1	collector
2	base
3	emitter



ORDERING INFORMATION

TYPE NUMBER		PACKAGE		
TIPE NOMBER	NAME DESCRIPTION V			
MPSA42	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54	
MPSA43				

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	MPSA42		_	300	V
	MPSA43		_	200	V
V _{CEO}	collector-emitter voltage	open base			
	MPSA42		_	300	V
	MPSA43		_	200	V
V _{EBO}	emitter-base voltage	open collector	_	6	V
I _C	collector current (DC)		_	100	mA
I _{CM}	peak collector current		_	200	mA
I _{BM}	peak base current		_	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	_	500	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	ambient temperature		-65	+150	°C

NPN high-voltage transistors

MPSA42; MPSA43

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	note 1	250	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector-base cut-off current				
	MPSA42	V _{CB} = 200 V; I _E = 0 A	_	100	nA
	MPSA43	V _{CB} = 160 V; I _E = 0 A	_	100	nA
I _{EBO}	emitter-base cut-off current				
	MPSA42	V _{EB} = 6 V; I _C = 0 A	_	100	nA
	MPSA43	$V_{EB} = 4 \text{ V}; I_{C} = 0 \text{ A}$	_	100	nA
h _{FE}	DC current gain	V _{CE} = 10 V; note 1			
		I _C = 1 mA	25	_	
		I _C = 10 mA	40	_	
		I _C = 30 mA	40	_	
V _{CEsat}	collector-emitter saturation voltage	I _C = 20 mA; I _B = 2 mA; note 1	_	500	mV
V _{BEsat}	base-emitter saturation voltage	I _C = 20 mA; I _B = 2 mA; note 1	_	900	mV
C _c	collector capacitance	$V_{CB} = 20 \text{ V}; I_E = i_e = 0 \text{ A}; f = 1 \text{ MHz}$			
	MPSA42		_	3	pF
	MPSA43		_	4	pF
f _T	transition frequency	$V_{CE} = 20 \text{ V}; I_{C} = 10 \text{ mA}; f = 100 \text{ MHz}$	50	-	MHz

Note

1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

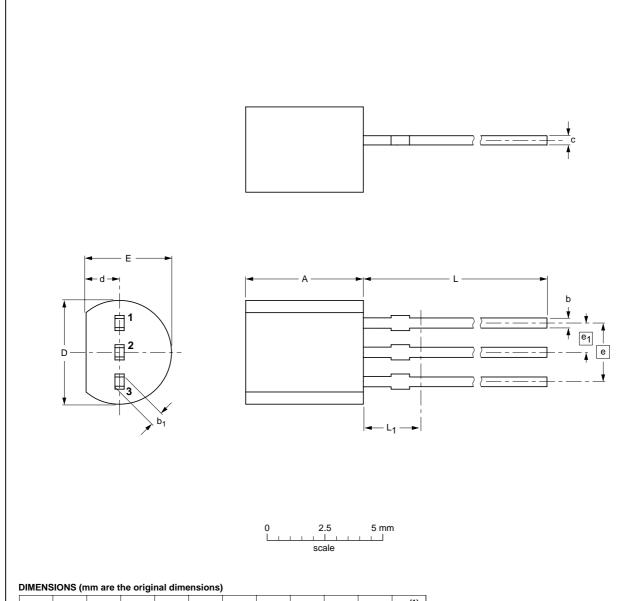
NPN high-voltage transistors

MPSA42; MPSA43

PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



UNIT	Α	b	b ₁	С	D	d	E	е	e ₁	L	L ₁ ⁽¹⁾ max.	
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5	

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE		REFER	ENCES	EUROPEAN ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT54		TO-92	SC-43A			04-06-28 04-11-16

NPN high-voltage transistors

MPSA42; MPSA43

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
- The product status of device(s) described in this document may have changed since this document was published
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Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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